arXiv:1304.3257v1 [cond-mat.mes-hall] 11 Apr 2013

Determination of the spin-orbit coupling in a nanowire via electric-dipole spin resonance

Rui Li,[1, 2] J. Q. You,[1, 2, 3] C. P. Sun,[1, 3] and Franco Nori[3, 4]
[1] *Beijing Computational Science Research Center, Beijing 100084, China*
[2] *Department of Physics and State Key Laboratory of Surface Physics, Fudan University, Shanghai 200433, China*
[3] *Center for Emergent Matter Science, RIKEN, Saitama 351-0198, Japan*
[4] *Physics Department, The University of Michigan, Ann Arbor, MI 48109-1040, USA*

(Dated: April 12, 2013)

A semiconductor nanowire quantum dot with strong spin-orbit coupling (SOC) can be used to achieve a spin-orbit qubit. In contrast to a spin qubit, the spin-orbit qubit can respond to an external a.c. electric field, an effect called electric-dipole spin resonance. Here we develop a theory that can apply in the strong SOC regime. We find that there is an optimal SOC strength $\eta_{\rm opt}=\sqrt{2}/2$, where the Rabi frequency induced by the a.c. electric field becomes maximal. Also, we show that both the level spacing and the Rabi frequency of the spin-orbit qubit have periodic responses to the direction of the external static magnetic field. These responses can be used to determine the SOC in the nanowire.

PACS numbers: 73.21.La, 71.70.Ej, 76.30.-v

Introduction.—How to achieve a simple and efficient way to manipulate a qubit is of basic importance in quantum information processing (see, e.g., [1, 2]). The spin-orbit qubit [3], unlike the conventional spin qubit [4], contains both the orbital degree of freedom and the spin degree of freedom of an electron, owing to the spin-orbit coupling (SOC) [5]. The spin-orbit qubit has an additional advantage of being manipulatable via an external a.c. electric field, an interesting phenomenon called the electric-dipole spin resonance (EDSR) [6–11]. With respect to generating a local a.c. magnetic field for manipulating a spin qubit, it is much easier to produce a local a.c. electric field with current experimental techniques.

The prerequisite for realizing a spin-orbit qubit in a semiconductor quantum-dot structure is the availability of SOC in the material [3]. The SOC appears when one takes a non-relativistic approximation to the Dirac equation [5]. There are two different types of SOC in a semiconductor material, i.e., the Rashba SOC due to structural inversion asymmetry [12], and the Dresselhaus SOC due to the bulk inversion asymmetry [13]. Usually, both types of SOC coexist in a material [14], but which one plays a major part depends on the properties of the material.

Semiconductor quantum wires with strong SOC, e.g., InSb nanowires [3, 11], is of current interest. It has been suggested as a potential platform for demonstrating Majorana quasiparticles [15, 16], and it can also be used to produce a quantum dot for achieving a spin-orbit qubit [3]. The coherent electric manipulation and the spectroscopy of a nanowire spin-orbit qubit were investigated [11], and a strong Rabi frequency of 100 MHz was also reported recently [17]. Interestingly, the frequency of the driving a.c. electric field depends on the direction of the applied static magnetic field [11]. As our study shows, this dependence is actually a signature of the strong SOC in the nanowire.

In this Letter, we provide an explicit theoretical explanation for the EDSR effect in a nanowire quantum dot with strong SOC. In comparison with previous theories, where the SOC was regarded as a perturbation [18–21], we consider a strong SOC. Instead, we treat the external static magnetic field as a perturbation. It is estimated that our theory can be valid when using a magnetic field as strong as 0.1 T. This field is much stronger than the magnetic field usually used in experiments on quantum devices, so the external magnetic field can indeed be used as a perturbation. With our theory applicable in the strong SOC regime, it reveals that the Rabi frequency induced by an external a.c. electric field has a maximum value at an optimal SOC strength, instead of the Rabi frequency that is linearly proportional to the SOC strength. As our theory shows, this linear dependence is only valid in the weak SOC regime. Also, our theory shows that the SOC can be probed by monitoring both the spectrum and the EDSR responses of the spin-orbit qubit to the direction of the external static magnetic field. Therefore, it can provide a useful method to determine both Rashba and Dresselhaus SOCs in the nanowire.

Spin-orbit qubit based on a nanowire quantum dot.—We consider a gated nanowire quantum dot with strong SOC, where an electron is confined in an one-dimensional harmonic well and subjected to a static magnetic field [22, 23]. The Hamiltonian reads

$$H=\frac{p^2}{2m_e}+\frac{1}{2}m_e\omega^2x^2+\alpha_R\sigma^yp+\alpha_D\sigma^xp+\frac{g_e\mu_BB}{2}\sigma^n,\quad(1)$$

where m_e is the effective electron mass, $p=-i\hbar\partial/\partial x$, $\alpha_{R(D)}$ is the Rashba (Dresselhaus) SOC strength, μ_B is Bohr magneton, and $\sigma^n\equiv\mathbf{n}\cdot\boldsymbol{\sigma}=\sigma^x\cos\theta+\sigma^y\sin\theta$, with $\mathbf{n}=(\cos\theta,\sin\theta)$ representing the direction of the external static magnetic field [see Fig. 1(a)]. Because

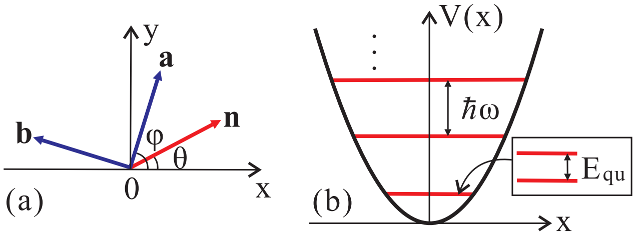

FIG. 1. (color online) (a) Schematical diagram of the unit vectors $\mathbf{n}$, $\mathbf{a}$, and $\mathbf{b}$, where $\mathbf{n} = (\cos\theta, \sin\theta)$ represents the direction of an external static magnetic field $\mathbf{B}$, $\mathbf{a} = (\cos\varphi, \sin\varphi)$, with $\varphi = \arctan(\alpha_R/\alpha_D) \in [0, \frac{\pi}{2}]$ characterizing the relative strength between the Rashba and Dresselhaus SOCs, and $\mathbf{b} = (-\sin\varphi, \cos\varphi)$ is a unit vector perpendicular to $\mathbf{a}$. (b) Energy spectrum of a semiconductor nanowire quantum dot modeled by H_0 in Eq. (2), where each energy level is two-fold degenerate. This degeneracy can be removed by applying a static magnetic field to the nanowire quantum dot. Here the lowest two levels with splitting $E_{\rm qu}$ are used to encode a spin-orbit qubit.

the electron moves in a one-dimensional well, the vector potential $\mathbf{A} = \frac{1}{2}\mathbf{B}\times\mathbf{r}$ has almost no effect on the orbital motion of the electron when the applied magnetic field is weak, i.e., $\omega \gg eB/(2m_e c)$.

Even though the Hamiltonian (1) looks simple, it is very difficult to analytically calculate its energy spectrum by directly solving the Schrödinger equation [24–26]. Therefore, in order to have a good understanding of the energy spectrum and the corresponding eigenstates of H, one has to rely on a perturbative method. Here, instead of α_R and α_D, we introduce two new parameters α and φ: $\alpha = \sqrt{\alpha_R^2 + \alpha_D^2}$, and $\varphi = \arctan(\alpha_R/\alpha_D)$, where $\varphi \in [0, \frac{\pi}{2}]$. With these new parameters, the Hamiltonian (1) can be rewritten as

$$\begin{aligned} H &= H_0 + H_1,\\ H_0 &= \frac{p^2}{2m_e} + \frac{1}{2}m_e\omega^2x^2 + \alpha\sigma^a p,\\ H_1 &= \frac{g_e\mu_B B}{2}[\cos(\theta-\varphi)\sigma^a + \sin(\theta-\varphi)\sigma^b], \end{aligned} \tag{2}$$

with $\sigma^c \equiv \mathbf{c}\cdot\boldsymbol{\sigma}$ ($\mathbf{c} = \mathbf{a}, \mathbf{b}, \mathbf{n}$). Here the unit vectors $\mathbf{a} = (\cos\varphi, \sin\varphi)$, $\mathbf{b} = (-\sin\varphi, \cos\varphi)$, and $\mathbf{n} = \cos(\theta-\varphi)\mathbf{a} + \sin(\theta-\varphi)\mathbf{b}$ are schematically illustrated in Fig. 1(a). In previous theories[18–21], the SOC term was often considered as a perturbation, but this applies only for a weak SOC, i.e., $\eta \equiv \sqrt{m_e/(\hbar\omega)}\alpha \ll 1$ in the nanowire quantum dot. Below we consider the case which is valid even in the strong SOC (i.e., large η) regime. Note that the Zeeman splitting $g_e\mu_B B$ ($\sim 1\mu$eV) is usually much less than the orbit splitting $\hbar\omega$ ($\sim$ 1–10 meV). For instance, in an InSb nanowire quantum dot, $\hbar\omega \approx 7.5$ meV, and $g_e \approx 40$ [11], so the external magnetic field can be as strong as $B \sim 0.1$ T for $\xi \equiv g_e\mu_B B/(\hbar\omega) \sim 0.03$. This field is much stronger than the magnetic field usually used in experiments [3, 11, 17], so H_1 can be treated as a perturbation. In this way, the Schrödinger equation of H can be analytically solved (see below), which is valid for both the strong SOC and the magnetic field usually used in experiments on quantum devices.

To encode a spin-orbit qubit, we only need to focus on the lowest two energy levels of H. Here we calculate the energy-level spacing and the Hilbert-space structure of the spin-orbit qubit by using the perturbative method for degenerate states [27], where all derived results are accurate up to first order in ξ.

It can be derived that a unitary transformation can diagonalize H_0, i.e., $e^{i(m_e\alpha/\hbar)x\sigma^a}H_0e^{-i(m_e\alpha/\hbar)x\sigma^a} = \frac{p^2}{2m_e} + \frac{1}{2}m_e\omega^2x^2 - m_e\alpha^2/2$. Let $\psi_n(x)$ be the eigenstates of a harmonic oscillator corresponding to the eigenvalues $(n+\frac{1}{2})\hbar\omega$, where $n = 0, 1, 2, \ldots$. Then, the eigenvalues of H_0 are $\varepsilon_n = (n+\frac{1}{2})\hbar\omega - \frac{1}{2}m_e\alpha^2$, and the corresponding eigenstates are given by

$$\begin{cases} |\Psi_{n\uparrow}\rangle = e^{-i(m_e\alpha/\hbar)x}\psi_n(x)|\uparrow_a\rangle,\\ |\Psi_{n\downarrow}\rangle = e^{i(m_e\alpha/\hbar)x}\psi_n(x)|\downarrow_a\rangle, \end{cases} \tag{3}$$

with $|\uparrow_a\rangle = (\sqrt{2}/2)(e^{-i\varphi/2}, e^{i\varphi/2})^T$, and $|\downarrow_a\rangle = (\sqrt{2}/2)(e^{-i\varphi/2}, -e^{i\varphi/2})^T$, where T denotes the transpose of a matrix, are two eigenstates of σ^a: $\sigma^a|\uparrow_a\rangle = |\uparrow_a\rangle$, and $\sigma^a|\downarrow_a\rangle = -|\downarrow_a\rangle$. The energy spectrum of H_0 is similar to the energy spectrum of a harmonic oscillator, except that each level ε_n is two-fold degenerate, with the corresponding degenerate eigenstates given by $|\Psi_{n\uparrow}\rangle$ and $|\Psi_{n\downarrow}\rangle$. Therefore, we should use the perturbative method for degenerate states, so as to calculate the energy spectrum and the corresponding eigenstates of H.

Our interest focuses on the $n = 0$ Hilbert subspace. Usually, the two degenerate states $|\Psi_{0\uparrow}\rangle$ and $|\Psi_{0\downarrow}\rangle$ will recombine in the zeroth-order wave functions, so we calculate H_1 in the Hilbert subspace spanned by $|\Psi_{0\uparrow}\rangle$ and $|\Psi_{0\downarrow}\rangle$:

$$H_1 = \frac{g_e\mu_B B}{2}\begin{pmatrix} \cos(\theta-\varphi) & ie^{-\eta^2}\sin(\theta-\varphi)\\ -ie^{-\eta^2}\sin(\theta-\varphi) & -\cos(\theta-\varphi) \end{pmatrix}. \tag{4}$$

Here we have used the formulas $\sigma^b|\uparrow_a\rangle = -i|\downarrow_a\rangle$, and $\sigma^b|\downarrow_a\rangle = i|\uparrow_a\rangle$ in deriving the above matrix. Diagonalizing this matrix, we obtain the eigenvalues and the corresponding eigenfunctions

$$\varepsilon_{0p}^{\pm} = \pm\tfrac{g_e\mu_B B}{2}f, \quad |\Psi_0^{\pm}\rangle = c_{\pm}|\Psi_{0\uparrow}\rangle + d_{\pm}|\Psi_{0\downarrow}\rangle, \tag{5}$$

where

$$\begin{aligned} c_{\pm} &= \frac{\cos(\theta-\varphi) \pm f}{\sqrt{2[f^2 \pm f\cos(\theta-\varphi)]}},\\ d_{\pm} &= \frac{-ie^{-\eta^2}\sin(\theta-\varphi)}{\sqrt{2[f^2 \pm f\cos(\theta-\varphi)]}}, \end{aligned} \tag{6}$$

with $f \equiv f(\eta, \theta-\varphi) = [\cos^2(\theta-\varphi) + e^{-2\eta^2}\sin^2(\theta-\varphi)]^{1/2}$. The wave functions $|\Psi_0^{\pm}\rangle$ are actually the recombined zeroth-order wave functions. The first-order wave functions can be calculated using the perturbative formula [27]: $|\Psi_{0p}^{\pm}\rangle = |\Psi_0^{\pm}\rangle + \sum_{n=1,\sigma=\uparrow,\downarrow}^{\infty} \frac{\langle\Psi_{n\sigma}|H_1|\Psi_0^{\pm}\rangle}{\varepsilon_0-\varepsilon_n}|\Psi_{n\sigma}\rangle$. Therefore, we obtain

$$\begin{aligned}|\Psi_{0p}^{\pm}\rangle &= c_{\pm}|\Psi_{0\uparrow}\rangle + d_{\pm}|\Psi_{0\downarrow}\rangle + i\frac{\xi}{2}e^{-\eta^2}\sin(\theta-\varphi)\\ &\times\sum_{n=1}^{\infty}\frac{\left(\sqrt{2}i\eta\right)^n}{n\sqrt{n!}}\left[(-1)^n c_{\pm}|\Psi_{n\downarrow}\rangle - d_{\pm}|\Psi_{n\uparrow}\rangle\right]. \quad (7)\end{aligned}$$

Here we have obtained the two lowest energy levels and the corresponding wave functions $|\Psi_{0p}^{\pm}\rangle$ of H by using degenerate perturbation theory, which are accurate up to first order in ξ. The two states $|\Psi_{0p}^{+}\rangle$ and $|\Psi_{0p}^{-}\rangle$ can be used to encode the spin-orbit qubit which has the level spacing [see Fig. 1(b)]:

$$E_{\text{qu}} = g_e\mu_B B\sqrt{\cos^2(\theta-\varphi) + e^{-2\eta^2}\sin^2(\theta-\varphi)}. \quad (8)$$

Clearly, it can be seen from Eq. (7) that the spin-orbit qubit is different from the conventional spin qubit (which only contains the $n = 0$ orbit state) because the spin-orbit qubit combines lots of orbit states ($n = 0, 1, \cdots, \infty$) with the spin state. This orbital feature of the spin-orbit qubit leads to an interesting phenomenon called EDSR, which can be used to manipulate the electron spin via an external a.c. electric field.

EDSR and its response to the magnetic-field direction.—In EDSR, the SOC plays a key role [8–11, 28], such that an electron spin can respond to an a.c. electric field. In previous studies, the SOC was treated as a perturbation, and the EDSR effect has been investigated for a quantum-well structure [18] and a two-dimensional GaAs quantum dot [19, 20]. Those results show that the Rabi frequency is linearly proportional to the SOC strength η [19]. Below we will show that this linear dependence of the Rabi frequency on η is due to the weak SOC.

When we apply an external a.c. electric field to the nanowire quantum dot, the total Hamiltonian becomes

$$\begin{aligned}H_{\text{tot}} = &\frac{p^2}{2m_e} + \frac{1}{2}m_e\omega^2x^2 + \alpha_R\sigma^y p + \alpha_D\sigma^x p + \frac{g_e\mu_B B}{2}\sigma^n\\ &+eEx\cos(2\pi\nu t), \quad (9)\end{aligned}$$

where ν is the frequency of the a.c. electric field. Based on the results derived above, when we focus on the Hilbert subspace of the spin-orbit qubit spanned by $|\Psi_{0p}^{+}\rangle$ and $|\Psi_{0p}^{-}\rangle$, the Hamiltonian is reduced to a spin-orbit qubit interacting with an a.c. electric field: $H_{\text{tot}} = \frac{1}{2}E_{\text{qu}}\tau^Z + eEx\cos(2\pi\nu t)$, where $\tau^Z = |\Psi_{0p}^{+}\rangle\langle\Psi_{0p}^{+}| - |\Psi_{0p}^{-}\rangle\langle\Psi_{0p}^{-}|$. In this Hilbert subspace of the spin-orbit qubit, x has the elements

$$\begin{aligned}&\langle\Psi_{0p}^{+}|x|\Psi_{0p}^{+}\rangle = 0 + \mathcal{O}(\xi^2), \quad \langle\Psi_{0p}^{-}|x|\Psi_{0p}^{-}\rangle = 0 + \mathcal{O}(\xi^2),\\ &\langle\Psi_{0p}^{+}|x|\Psi_{0p}^{-}\rangle = -ix_0\xi\eta\, e^{-\eta^2}|\sin(\theta-\varphi)| + \mathcal{O}(\xi^2), \quad (10)\end{aligned}$$

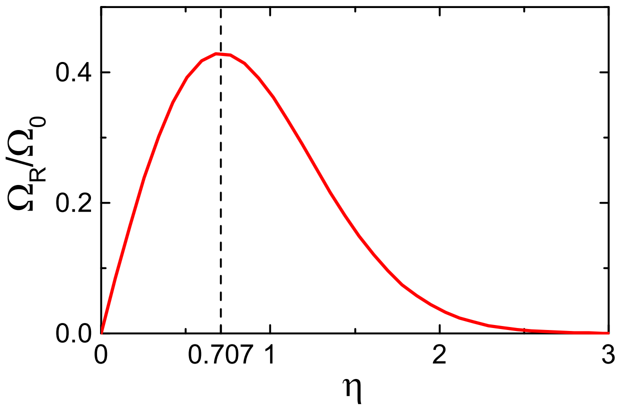

FIG. 2. (color online) Dependence of the Rabi frequency (in units of Ω_0) on the SOC strength η, where $\Omega_0 = (eEx_0/h)\xi|\sin(\theta-\varphi)|$. There is an optimal SOC strength $\eta_{\text{opt}} = \sqrt{2}/2 \approx 0.707$, where the Rabi frequency becomes maximal. After this optimal point η_{opt}, increasing SOC reduces the Rabi frequency.

where $x_0 = \sqrt{\hbar/(m_e\omega)}$. Thus, we conclude that H_{tot} can be reduced to the following EDSR Hamiltonian:

$$H_{\text{tot}} = \frac{1}{2}E_{\text{qu}}\tau^Z + h\Omega_R\tau^Y\cos(2\pi\nu t), \quad (11)$$

where

$$\Omega_R = \left(\frac{eEx_0}{h}\right)\xi\eta\, e^{-\eta^2}|\sin(\theta-\varphi)|, \quad (12)$$

is the Rabi frequency, with h being the Planck constant, and $\tau^Y = i(|\Psi_{0p}^{-}\rangle\langle\Psi_{0p}^{+}| - |\Psi_{0p}^{+}\rangle\langle\Psi_{0p}^{-}|)$. When η is treated as a perturbation for the weak SOC ($\eta \ll 1$), we can expand Ω_R as $\Omega_R = (eEx_0/h)\xi\eta|\sin(\theta-\varphi)| + \mathcal{O}(\eta^2)$, so we recover the previous result [19]. In fact, this EDSR Hamiltonian is the Rabi-oscillation Hamiltonian in quantum optics [29], where a quantum two-level system interacts with a classical field. Therefore, the physics of EDSR is transparent: when the driving frequency is in resonance to the level spacing of the spin-orbit qubit ($h\nu = E_{\text{qu}}$), the spin-orbit qubit can be flipped from one basis state to another via the Rabi oscillation, where Ω_R^{-1} characterizes the manipulation time.

Note that the SOC strength η is not treated as a perturbation in our theory, so our results apply in the strong SOC regime. Firstly, the level spacing E_{qu} given in Eq. (8) depends on the direction θ of the external static magnetic field. If η is treated as a perturbation as for a weak SOC, the level spacing is just the Zeeman splitting $g_e\mu_B B$. Thus, the dependence of E_{qu} on the magnetic-field direction is a signature of strong SOC in the nanowire. This directional dependence was demonstrated in a recent experiment on an InSb nanowire quantum dot [11]. Secondly, the Rabi frequency Ω_R given in Eq. (12) is not linearly proportional to the SOC

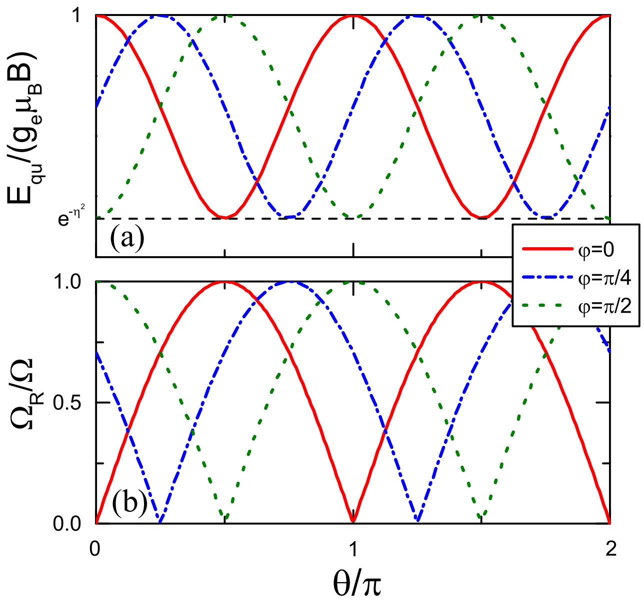

FIG. 3. (color online) (a) Periodic response of the level spacing $E_{\rm qu}$ (in units of $g_e\mu_B B$) of the spin-orbit qubit on the direction θ of the external static magnetic field. (b) Periodic response of the Rabi frequency Ω_R (in units of Ω) on the direction θ of the external static magnetic field, where $\Omega = (eEx_0/h)\xi\eta\, e^{-\eta^2}$. The parameter $\varphi = \arctan(\alpha_R/\alpha_D)$ characterizes the relative strength between the Rashba and Dresselhaus SOCs in the nanowire. For example, $\varphi = 0$ corresponds to a nanowire with pure Dresselhaus SOC ($\alpha_R = 0$), $\varphi = \pi/2$ corresponds to a nanowire with pure Rashba SOC ($\alpha_D = 0$), and $\varphi = \pi/4$ corresponds to a nanowire with equal Rashba and Dresselhaus SOCs ($\alpha_R = \alpha_D$).

strength η. Instead, there is an optimal SOC strength $\eta_{\rm opt} = \sqrt{2}/2$, at which the Rabi frequency reaches its maximum value (see Fig. 2). Our results imply that, in order to achieve the strongest Rabi frequency, it is not necessary to find materials with extremely strong SOC, but to find a material with an optimal value of the SOC strength $\eta_{\rm opt} = \sqrt{2}/2$. This optimal material gives the least manipulation time Ω_R^{-1} for the state flipping of a spin-orbit qubit.

The determination of the SOC is an important goal [30]. Because both level spacing and Rabi frequency of the spin-orbit qubit depend on the direction of the external static magnetic field, we can use this response to determine both the Rashba and Dresselhaus SOC strengths, α_R and α_D, in the nanowire. Figure 3 shows the dependence of both the level splitting and the Rabi frequency on the magnetic-field direction for different values of $\varphi = \arctan(\alpha_R/\alpha_D)$. Because the level splitting $E_{\rm qu}$ oscillates between $e^{-\eta^2}$ and 1 [see Fig. 3(a)], we can determine the SOC strength η from the minimal amplitude $e^{-\eta^2}$. Moreover, by monitoring how the level splitting $E_{\rm qu}$ and the Rabi frequency Ω_R vary with the direction θ of the external static magnetic field, we can determine the parameter φ. For example, the level spacing $E_{\rm qu}$ in Eq. (8) reaches its maximum values at $\theta_{\rm max} = \pm l\pi + \varphi$ ($l = 0, 1, 2\cdots$) [see Fig. 3(a)], and the Rabi frequency Ω_R in Eq. (12) reaches its maximum values at $\theta_{\rm max} = \pm(2l+1)\pi/2 + \varphi$ ($l = 0, 1, 2, \cdots$) [see Fig. 3(b)]. Thus, φ can be determined from the values of $\theta_{\rm max}$. Because $\alpha_D = \alpha\cos\varphi$, and $\alpha_R = \alpha\sin\varphi$, with $\alpha = \eta\sqrt{\hbar\omega/m_e}$, we should know the orbit-level spacing $\hbar\omega$ to obtain the Rashba and Dresselhaus SOC strengths, α_R and α_D, in the nanowire. Actually, the orbit-level spacing $\hbar\omega$ is controlled by the gate voltages on the static electric gates which are used to form the trap potential $\frac{1}{2}m_e\omega^2x^2$. We take a recent experiment as an example. By comparing Fig. 3(a) with Fig. 2(c) in [11], we obtain $e^{-\eta^2} \approx 15/20$ and $\theta_{\rm max} \approx 0.22\pi$ at $l = 0$ from the experimental data. Thus, we have $\eta \approx 0.54$ and $\varphi = \theta_{\rm max} \approx 0.22\pi$ (40°) for the nanowire material. Also, this value of $\eta \approx 0.54$ reveals that the nanowire material used in [11] has a strong SOC.

Conclusions.—We have theoretically investigated the EDSR effect in a semiconductor nanowire quantum dot with strong SOC. In contrast to the previous theories developed in the weak-SOC regime, our results demonstrate that there is an optimal SOC strength $\eta_{\rm opt} = \sqrt{2}/2$ where the Rabi frequency induced by the external a.c. electric field is maximal. Also, we show that both the level spacing and the Rabi frequency of the spin-orbit qubit have periodic responses to the direction of the external static magnetic field. These responses can be used to probe the SOC in the nanowire by determining both the Rashba and Dresselhaus SOC strengths in the material.

R.L. and J.Q.Y. are partially supported by the National Basic Research Program of China Grant No. 2009CB929302 and the National Natural Science Foundation of China Grant No. 91121015. F.N. is partially supported by the ARO, JSPS-RFBR contract No. 12-02-92100, Grant-in-Aid for Scientific Research (S), MEXT Kakenhi on Quantum Cybernetics, and the JSPS via its FIRST program.

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